# **TL594**

# Precision Switchmode Pulse Width Modulation Control Circuit

The TL594 is a fixed frequency, pulse width modulation control circuit designed primarily for Switchmode power supply control.

### **Features**

- Complete Pulse Width Modulation Control Circuitry
- On-Chip Oscillator with Master or Slave Operation
- On–Chip Error Amplifiers
- On-Chip 5.0 V Reference, 1.5% Accuracy
- Adjustable Deadtime Control
- Uncommitted Output Transistors Rated to 500 mA Source or Sink
- Output Control for Push-Pull or Single-Ended Operation
- Undervoltage Lockout
- Pb-Free Packages are Available\*

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Power Supply Voltage	V <sub>CC</sub>	42	٧
Collector Output Voltage	V <sub>C1</sub> , V <sub>C2</sub>	42	V
Collector Output Current (Each Transistor) (Note 1)	I <sub>C1</sub> , I <sub>C2</sub>	500	mA
Amplifier Input Voltage Range	V <sub>IR</sub>	-0.3 to +42	V
Power Dissipation @ T <sub>A</sub> ≤ 45°C	$P_{D}$	1000	mW
Thermal Resistance Junction-to-Ambient (PDIP) Junction-to-Air (TSSOP) Junction-to-Ambient (SOIC)	$R_{ hetaJA}$	80 140 135	°C/W
Operating Junction Temperature	TJ	125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +125	°C
Operating Ambient Temperature Range TL594CD, CN, CDTB	T <sub>A</sub>	-40 to 85	°C
Derating Ambient Temperature	T <sub>A</sub>	45	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

Maximum thermal limits must be observed.



# ON Semiconductor®

http://onsemi.com

## MARKING DIAGRAMS

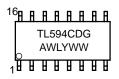


PDIP-16 N SUFFIX CASE 648





SO-16 D SUFFIX CASE 751B





TSSOP-16 DTB SUFFIX CASE 948F



A = Assembly Location

WL, L = Wafer Lot

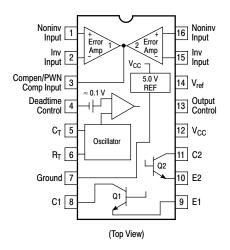
YY, Y = Year

WW, W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

## **PIN CONNECTIONS**



# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# **TL594**

# **RECOMMENDED OPERATING CONDITIONS**

Characteristics	Symbol	Min	Тур	Max	Unit
Power Supply Voltage	V <sub>CC</sub>	7.0	15	40	V
Collector Output Voltage	V <sub>C1</sub> , V <sub>C2</sub>	_	30	40	V
Collector Output Current (Each transistor)	I <sub>C1</sub> , I <sub>C2</sub>	_	-	200	mA
Amplified Input Voltage	V <sub>in</sub>	0.3	-	V <sub>CC</sub> - 2.0	V
Current Into Feedback Terminal	I <sub>fb</sub>	_	_	0.3	mA
Reference Output Current	I <sub>ref</sub>	_	_	10	mA
Timing Resistor	R <sub>T</sub>	1.8	30	500	kΩ
Timing Capacitor	C <sub>T</sub>	0.0047	0.001	10	μF
Oscillator Frequency	f <sub>osc</sub>	1.0	40	300	kHz
PWM Input Voltage (Pins 3, 4, 13)	_	0.3	-	5.3	V

**ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = 15 V,  $C_T$  = 0.01  $\mu$ F,  $R_T$  = 12  $k\Omega$ , unless otherwise noted.) For typical values  $T_A$  = 25°C, for min/max values  $T_A$  is the operating ambient temperature range that applies, unless otherwise noted.

Characteristics	Symbol	Min	Тур	Max	Unit
REFERENCE SECTION	1				
Reference Voltage ( $I_O = 1.0 \text{ mA}, T_A = 25^{\circ}\text{C}$ ) ( $I_O = 1.0 \text{ mA}$ )	V <sub>ref</sub>	4.925 4.9	5.0 –	5.075 5.1	V
Line Regulation (V <sub>CC</sub> = 7.0 V to 40 V)	Reg <sub>line</sub>	-	2.0	25	mV
Load Regulation (I <sub>O</sub> = 1.0 mA to 10 mA)	Reg <sub>load</sub>	-	2.0	15	mV
Short Circuit Output Current (V <sub>ref</sub> = 0 V)	I <sub>SC</sub>	15	40	75	mA
OUTPUT SECTION					
Collector Off–State Current (V <sub>CC</sub> = 40 V, V <sub>CE</sub> = 40 V)	I <sub>C(off)</sub>	-	2.0	100	μΑ
Emitter Off-State Current (V <sub>CC</sub> = 40 V, V <sub>C</sub> = 40 V, V <sub>E</sub> = 0 V)	I <sub>E(off)</sub>	_	_	-100	μΑ
Collector–Emitter Saturation Voltage (Note 1) Common–Emitter ( $V_E = 0 \text{ V, } I_C = 200 \text{ mA}$ ) Emitter–Follower ( $V_C = 15 \text{ V, } I_E = -200 \text{ mA}$ )	V <sub>SAT(C)</sub> V <sub>SAT(E)</sub>	_ _	1.1 1.5	1.3 2.5	V
Output Control Pin Current Low State ( $V_{OC} \le 0.4 \text{ V}$ ) High State ( $V_{OC} = V_{ref}$ )	I <sub>OCL</sub> I <sub>OCH</sub>	_ _	0.1 2.0	- 20	μΑ
Output Voltage Rise Time Common–Emitter (See Figure 13) Emitter–Follower (See Figure 14)	t <sub>r</sub>	- -	100 100	200 200	ns
Output Voltage Fall Time Common–Emitter (See Figure 13) Emitter–Follower (See Figure 14)	t <sub>f</sub>	_ _	40 40	100 100	ns
ERROR AMPLIFIER SECTION					
Input Offset Voltage (V <sub>O (Pin 3)</sub> = 2.5 V)	V <sub>IO</sub>	-	2.0	10	mV
Input Offset Current (V <sub>O (Pin 3)</sub> = 2.5 V)	I <sub>IO</sub>	-	5.0	250	nA
Input Bias Current (V <sub>O (Pin 3)</sub> = 2.5 V)	I <sub>IB</sub>	-	-0.1	-1.0	μΑ
Input Common Mode Voltage Range (V <sub>CC</sub> = 40 V, T <sub>A</sub> = 25°C)	V <sub>ICR</sub>	(	to V <sub>CC</sub> -2.	0	V
Inverting Input Voltage Range	V <sub>IR(INV)</sub>	-(	).3 to V <sub>CC</sub> -2	2.0	V
Open Loop Voltage Gain ( $\Delta V_O = 3.0 \text{ V}$ , $V_O = 0.5 \text{ V}$ to $3.5 \text{ V}$ , $R_L = 2.0 \text{ k}\Omega$ )	A <sub>VOL</sub>	70	95	-	dB
Unity–Gain Crossover Frequency ( $V_O = 0.5 \text{ V}$ to 3.5 V, $R_L = 2.0 \text{ k}\Omega$ )	f <sub>C</sub>	-	700	-	kHz
Phase Margin at Unity–Gain ( $V_0 = 0.5 \text{ V}$ to 3.5 V, $R_L = 2.0 \text{ k}\Omega$ )	φm	-	65	-	deg.
Common Mode Rejection Ratio (V <sub>CC</sub> = 40 V)	CMRR	65	90	-	dB
Power Supply Rejection Ratio ( $\Delta V_{CC} = 33 \text{ V}, V_{O} = 2.5 \text{ V}, R_{L} = 2.0 \text{ k}\Omega$ )	PSRR	_	100	_	dB
Output Sink Current (V <sub>O (Pin 3)</sub> = 0.7 V)	I <sub>0</sub> -	0.3	0.7	_	mA
Output Source Current (V <sub>O (Pin 3)</sub> = 3.5 V)	l <sub>0</sub> +	-2.0	-4.0	_	mA

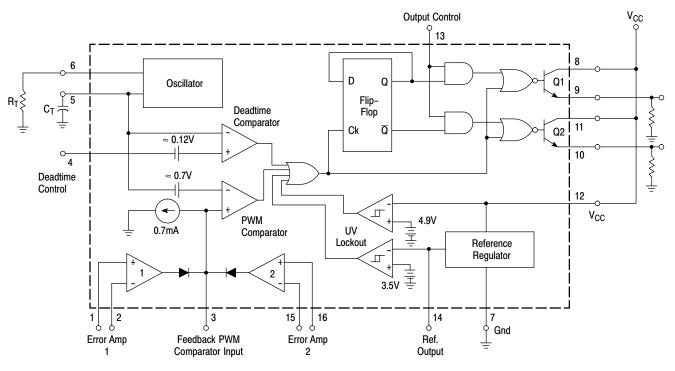
<sup>1.</sup> Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

# **TL594**

**ELECTRICAL CHARACTERISTICS** ( $V_{CC}$  = 15 V,  $C_T$  = 0.01  $\mu$ F,  $R_T$  = 12  $k\Omega$ , unless otherwise noted.) For typical values  $T_A$  = 25°C, for min/max values  $T_A$  is the operating ambient temperature range that applies, unless otherwise noted.

Characteristics	Symbol	Min	Тур	Max	Unit
PWM COMPARATOR SECTION (Test Circuit Figure 11)					
Input Threshold Voltage (Zero Duty Cycle)	$V_{TH}$	_	3.6	4.5	V
Input Sink Current (V <sub>Pin 3</sub> = 0.7 V)	I <sub>I</sub> _	0.3	0.7	-	mA
DEADTIME CONTROL SECTION (Test Circuit Figure 11)					
Input Bias Current (Pin 4) (V <sub>Pin 4</sub> = 0 V to 5.25 V)	I <sub>IB (DT)</sub>	-	-2.0	-10	μΑ
Maximum Duty Cycle, Each Output, Push–Pull Mode ( $V_{Pin~4}=0~V,~C_{T}=0.01~\mu\text{F},~R_{T}=12~k\Omega$ ) ( $V_{Pin~4}=0~V,~C_{T}=0.001~\mu\text{F},~R_{T}=30~k\Omega$ )	DC <sub>max</sub>	45 -	48 45	50 -	%
Input Threshold Voltage (Pin 4) (Zero Duty Cycle) (Maximum Duty Cycle)	V <sub>TH</sub>	_ 0	2.8	3.3	V
OSCILLATOR SECTION					
Frequency $ \begin{array}{l} (C_T=0.001~\mu\text{F},~R_T=30~k\Omega) \\ (C_T=0.01~\mu\text{F},~R_T=12~k\Omega,~T_A=25^{\circ}\text{C}) \\ (C_T=0.01~\mu\text{F},~R_T=12~k\Omega,~T_A=T_{low}~\text{to}~T_{high}) \end{array} $	f <sub>osc</sub>	9.2 9.0	40 10 -	- 10.8 12	kHz
Standard Deviation of Frequency* ( $C_T$ = 0.001 $\mu$ F, $R_T$ = 30 $k\Omega$ )	σf <sub>osc</sub>	_	1.5	-	%
Frequency Change with Voltage (V <sub>CC</sub> = 7.0 V to 40 V, T <sub>A</sub> = 25°C)	$\Delta f_{OSC} (\Delta V)$	-	0.2	1.0	%
Frequency Change with Temperature $(\Delta T_A = T_{low} \text{ to } T_{high}, \ C_T = 0.01 \ \mu\text{F}, \ R_T = 12 \ \text{k}\Omega)$	$\Delta f_{OSC} (\Delta T)$	-	4.0	-	%
UNDERVOLTAGE LOCKOUT SECTION					
Turn–On Threshold ( $V_{CC}$ Increasing, $I_{ref}$ = 1.0 mA) $T_A$ = 25°C $T_A$ = $T_{low}$ to $T_{high}$	V <sub>th</sub>	4.0 3.5	5.2	6.0 6.5	V
Hysteresis TL594C,I TL594M	V <sub>H</sub>	100 50	150 150	300 300	mV
TOTAL DEVICE					
Standby Supply Current (Pin 6 at $V_{ref}$ , All other inputs and outputs open) ( $V_{CC}$ = 15 V) ( $V_{CC}$ = 40 V)	I <sub>CC</sub>	= -	8.0 8.0	15 18	mA
Average Supply Current (V <sub>Pin 4</sub> = 2.0 V, C <sub>T</sub> = 0.01 $\mu$ F, R <sub>T</sub> = 12 k $\Omega$ , V <sub>CC</sub> = 15 V, See Figure 11)		-	11	_	mA

\*Standard deviation is a measure of the statistical distribution about the mean as derived from the formula,  $\sigma = \frac{\sum_{i=1}^{N} (X_i - \overline{X})^2}{N-1}$ 



This device contains 46 active transistors.

Figure 1. Representative Block Diagram

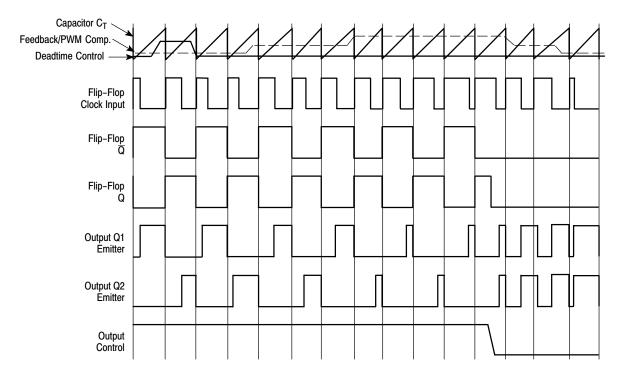


Figure 2. Timing Diagram

### APPLICATIONS INFORMATION

# Description

The TL594 is a fixed–frequency pulse width modulation control circuit, incorporating the primary building blocks required for the control of a switching power supply. (See Figure 1) An internal–linear sawtooth oscillator is frequency–programmable by two external components, R<sub>T</sub> and C<sub>T</sub>. The approximate oscillator frequency is determined by:

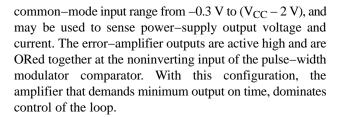
$$f_{OSC} \approx \frac{1.1}{R_T \bullet C_T}$$

For more information refer to Figure 3.

Output pulse width modulation is accomplished by comparison of the positive sawtooth waveform across capacitor  $C_T$  to either of two control signals. The NOR gates, which drive output transistors Q1 and Q2, are enabled only when the flip—flop clock—input line is in its low state. This happens only during that portion of time when the sawtooth voltage is greater than the control signals. Therefore, an increase in control—signal amplitude causes a corresponding linear decrease of output pulse width. (Refer to the Timing Diagram shown in Figure 2.)

The control signals are external inputs that can be fed into the deadtime control, the error amplifier inputs, or the feedback input. The deadtime control comparator has an effective 120 mV input offset which limits the minimum output deadtime to approximately the first 4% of the sawtooth–cycle time. This would result in a maximum duty cycle on a given output of 96% with the output control grounded, and 48% with it connected to the reference line. Additional deadtime may be imposed on the output by setting the deadtime–control input to a fixed voltage, ranging between 0 V to 3.3 V.

The pulse width modulator comparator provides a means for the error amplifiers to adjust the output pulse width from the maximum percent on—time, established by the deadtime control input, down to zero, as the voltage at the feedback pin varies from 0.5 V to 3.5 V. Both error amplifiers have a



**Functional Table** 

Input/Output Controls	Output Function	$\frac{f_{\text{out}}}{f_{\text{osc}}} =$
Grounded	Single-ended PWM @ Q1 and Q2	1.0
@ V <sub>ref</sub>	Push-pull Operation	0.5

When capacitor C<sub>T</sub> is discharged, a positive pulse is generated on the output of the deadtime comparator, which clocks the pulse-steering flip-flop and inhibits the output transistors, Q1 and Q2. With the output-control connected to the reference line, the pulse-steering flip-flop directs the modulated pulses to each of the two output transistors alternately for push-pull operation. The output frequency is equal to half that of the oscillator. Output drive can also be taken from Q1 or Q2, when single-ended operation with a maximum on-time of less than 50% is required. This is desirable when the output transformer has a ringback winding with a catch diode used for snubbing. When higher output-drive currents are required for single-ended operation, Q1 and Q2 may be connected in parallel, and the output-mode pin must be tied to ground to disable the flip-flop. The output frequency will now be equal to that of the oscillator.

The TL594 has an internal 5.0 V reference capable of sourcing up to 10 mA of load current for external bias circuits. The reference has an internal accuracy of  $\pm 1.5\%$  with a typical thermal drift of less than 50 mV over an operating temperature range of  $0^{\circ}$  to  $70^{\circ}$ C.

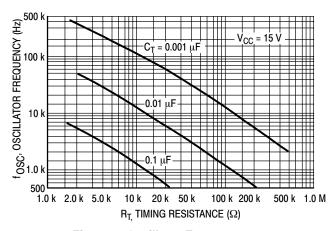


Figure 3. Oscillator Frequency versus Timing Resistance

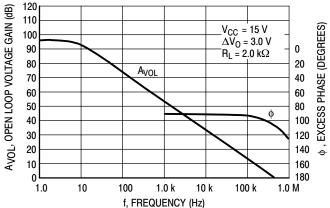


Figure 4. Open Loop Voltage Gain and Phase versus Frequency

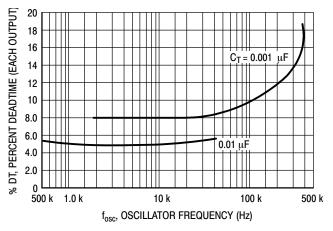


Figure 5. Percent Deadtime versus Oscillator Frequency

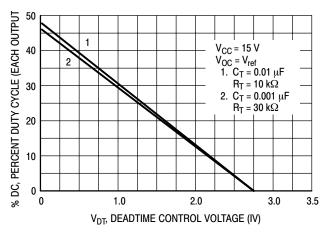


Figure 6. Percent Duty Cycle versus Deadtime Control Voltage

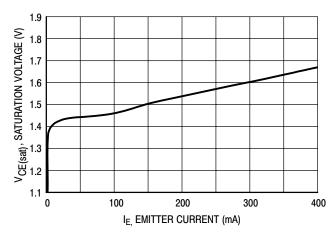


Figure 7. Emitter–Follower Configuration
Output Saturation Voltage versus
Emitter Current

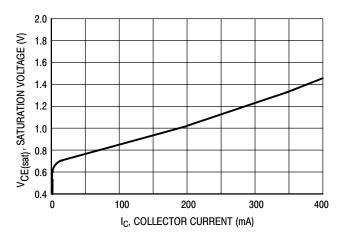


Figure 8. Common–Emitter Configuration
Output Saturation Voltage versus
Collector Current

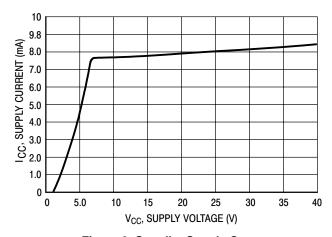


Figure 9. Standby Supply Current versus Supply Voltage

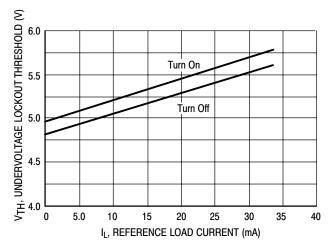


Figure 10. Undervoltage Lockout Thresholds versus Reference Load Current

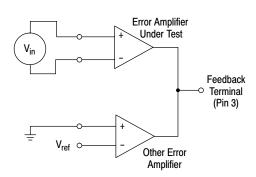


Figure 11. Error-Amplifier Characteristics

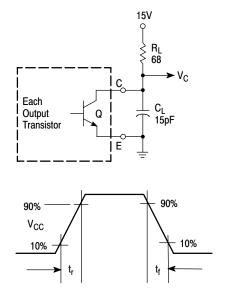


Figure 13. Common–Emitter Configuration
Test Circuit and Waveform

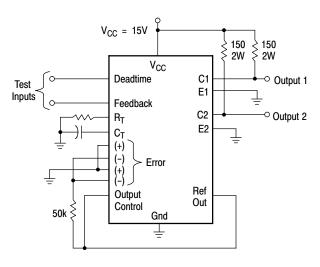


Figure 12. Deadtime and Feedback Control Circuit

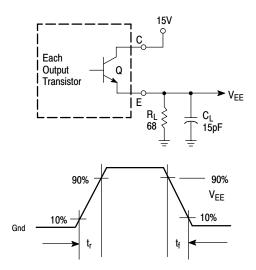


Figure 14. Emitter–Follower Configuration Test Circuit and Waveform

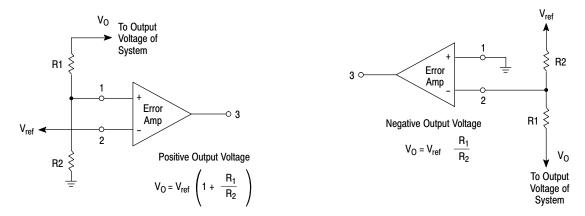


Figure 15. Error-Amplifier Sensing Techniques

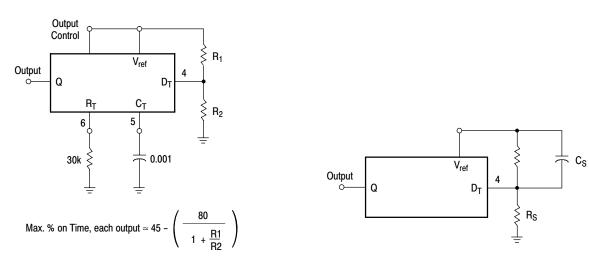


Figure 16. Deadtime Control Circuit

Figure 17. Soft-Start Circuit

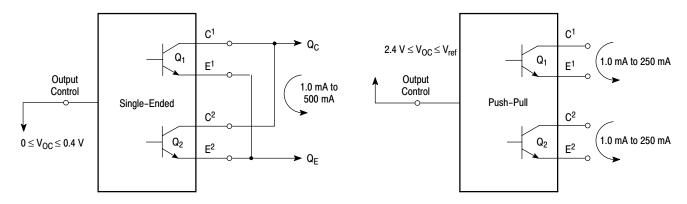


Figure 18. Output Connections for Single-Ended and Push-Pull Configurations

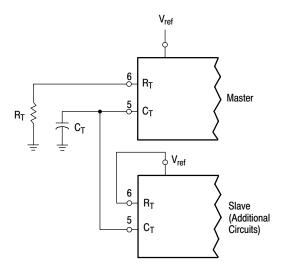


Figure 19. Slaving Two or More Control Circuits

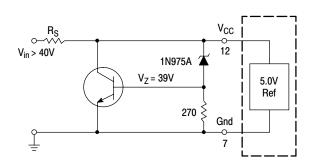


Figure 20. Operation with  $V_{in} > 40 \text{ V}$  Using External Zener

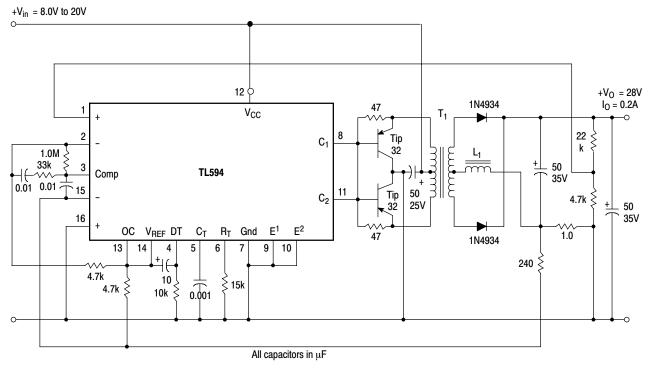


Figure 21. Pulse Width Modulated Push-Pull Converter

Test	Conditions	Results	14 25 mH @ 0.2 A
Line Regulation	V <sub>in</sub> = 10 V to 40 V	14 mV 0.28%	L1 – 3.5 mH @ 0.3 A T1 – Primary: 20T C.T. #28 AWG
Load Regulation	$V_{in} = 28 \text{ V}, I_{O} = 1.0 \text{ mA to } 1.0 \text{ A}$	3.0 mV 0.06%	Secondary: 12OT C.T. #36 AWG Core: Ferroxcube 1408P-L00-3CB
Output Ripple	V <sub>in</sub> = 28 V, I <sub>O</sub> = 1.0 A	65 mVpp P.A.R.D.	
Short Circuit Current	$V_{in}$ = 28 V, $R_L$ = 0.1 $\Omega$	1.6 A	
Efficiency	V <sub>in</sub> = 28 V, I <sub>O</sub> = 1.0 A	71%	

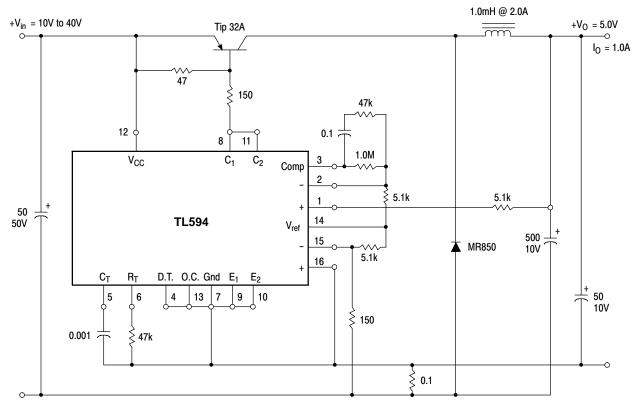


Figure 22. Pulse Width Modulated Step-Down Converter

Test	Conditions	Results	
Line Regulation	V <sub>in</sub> = 8.0 V to 40 V	3.0 mV 0.01%	
Load Regulation	$V_{in} = 12.6 \text{ V}, I_{O} = 0.2 \text{ mA to } 200 \text{ mA}$	5.0 mV 0.02%	
Output Ripple	V <sub>in</sub> = 12.6 V, I <sub>O</sub> = 200 mA	40 mVpp P.A.R.D.	
Short Circuit Current	$V_{in}$ = 12.6 V, $R_L$ = 0.1 $\Omega$	250 mA	
Efficiency	V <sub>in</sub> = 12.6 V, I <sub>O</sub> = 200 mA	72%	

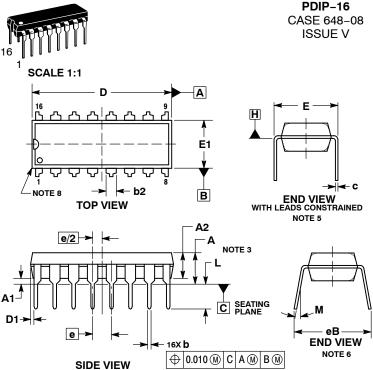
# **ORDERING INFORMATION**

Device	Operating Temperature Range	Package	Shipping <sup>†</sup>
TL594CD	−40 to 85°C	SOIC-16	48 Units/Rail
TL594CDG	−40 to 85°C	SOIC-16 (Pb-Free)	48 Units/Rail
TL594CDR2	−40 to 85°C	SOIC-16	2400 Tape & Reel
TL594CDR2G	−40 to 85°C	SOIC-16 (Pb-Free)	2400 Tape & Reel
TL594CN	−40 to 85°C	PDIP-16	25 Units/Rail
TL594CNG	−40 to 85°C	PDIP-16 (Pb-Free)	25 Units/Rail
TL594CDTBG*	−40 to 85°C	TSSOP-16*	96 Units/Rail
TL594CDTBR2G	−40 to 85°C	TSSOP-16*	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

# **MECHANICAL CASE OUTLINE**



PDIP-16

**DATE 22 APR 2015** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- DIMENSIONING AND TOLERANGING FER ASME 114-3M, 1994
  CONTROLLING DIMENSION: INCHES.

  DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.

  DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH
  OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
  NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE
- LEADS, WHERE THE LEADS EXIT THE BODY.

  PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54	BSC
eB		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

# **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code

= Assembly Location

WL = Wafer Lot YY = Year

WW = Work Week

G = Pb-Free Package

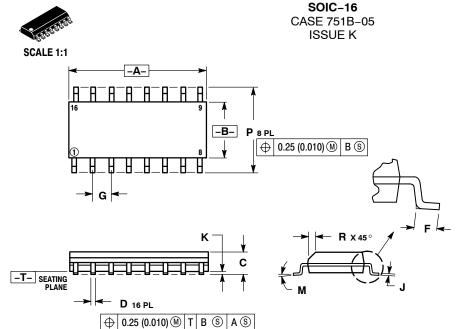
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1	:	STYLE 2	:
PIN 1.	CATHODE	PIN 1.	COMMON DRAIN
2.	CATHODE	2.	COMMON DRAIN
3.	CATHODE	3.	COMMON DRAIN
4.	CATHODE	4.	COMMON DRAIN
5.	CATHODE	5.	COMMON DRAIN
6.	CATHODE	6.	COMMON DRAIN
7.	CATHODE	7.	COMMON DRAIN
8.	CATHODE	8.	COMMON DRAIN
9.	ANODE	9.	GATE
10.	ANODE	10.	SOURCE
11.	ANODE	11.	GATE
12.	ANODE	12.	SOURCE
13.	ANODE	13.	GATE
14.	ANODE	14.	SOURCE
15.	ANODE	15.	GATE
16.	ANODE	16.	SOURCE

DOCUMENT NUMBER:	98ASB42431B Electronic versions are uncontrolled except when accessed directly from the Printed versions are uncontrolled except when stamped "CONTROLLED COF		
DESCRIPTION:	PDIP-16		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

# **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

2. 3.	COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE COLLECTOR COLLECTOR BASE EMITTER NO CONNECTION EMITTER BASE EMITTER BASE EMITTER BASE	2. 3. 4. 5. 6. 7. 8. 9. 10.	CATHODE ANODE	2. 3. 4. 5. 6. 7. 8. 9. 10.	COLLECTOR, DYE #1 BASE, #1 EMITTER, #1 COLLECTOR, #1 COLLECTOR, #2 BASE, #2 EMITTER, #2 COLLECTOR, #2 COLLECTOR, #2 COLLECTOR, #3	STYLE 4: PIN 1. 2. 3. 4. 5. 6. 7. 8. 9. 10. 11. 12. 13.	COLLECTOR, DYN COLLECTOR, #1 COLLECTOR, #2 COLLECTOR, #3 COLLECTOR, #3 COLLECTOR, #4 COLLECTOR, #4 BASE, #4 EMITTER, #4 BASE, #3 EMITTER, #3 BASE, #2		
14.	COLLECTOR		NO CONNECTION	14.		14.		SOLDERING	FOOTPRINT
15.	EMITTER		ANODE	15.		15.	BASE, #1	8	X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		^ 40 <del></del>
					,		,		6X 1.12
STYLE 5:	DDAIN DVE #4	STYLE 6:	OATHODE	STYLE 7:	COURCE N OU			'	0.1.12
PIN 1.	DRAIN, DYE #1	PIN 1.		PIN 1.	SOURCE N-CH	Τ\		<u></u>	16
2.	DRAIN, #1	2. 3.	CATHODE CATHODE	2.	COMMON DRAIN (OUTPU			↓ └──	10
3. 4.	DRAIN, #2 DRAIN, #2	3. 4.	CATHODE	3. 4.	COMMON DRAIN (OUTPU' GATE P-CH	1)		<u>*</u>	
4. 5.	DRAIN, #2 DRAIN, #3	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\			
5. 6.	DRAIN, #3	5. 6.	CATHODE	6.	COMMON DRAIN (OUTPU		1	.58 <b>∱</b>	
7.	DRAIN, #4	7.		7.	COMMON DRAIN (OUTPU		U.	.58	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	.,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	,	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)			
13.	GATE, #2	13.	ANODE	13.	GATE N-CH				
14.	SOURCE, #2	14.	ANODE	14.	COMMON DRAIN (OUTPU	T)			—— ↓ PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU	T)			<u>+-+</u> -
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH				
								8	9 ++ 7
								,	DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42566B	SB42566B Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				
DESCRIPTION:	SOIC-16		PAGE 1 OF 1			

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

☐ 0.10 (0.004)

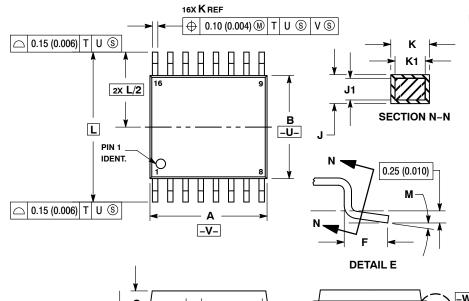
D

-T- SEATING PLANE



TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



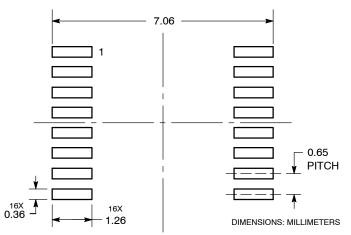
#### NOTES

- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	٥°	QΟ	٥°	gο	



G



## **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70247A Electronic versions are uncontrolled except when accessed directly from the Document Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	TSSOP-16		PAGE 1 OF 1	

**DETAIL E** 

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative